Renesas Electronics America Inc - R5F212D7SDFP#V2 Datasheet

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Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	R8C
Core Size	16-Bit
Speed	20MHz
Connectivity	I²C, LINbus, SIO, SSU, UART/USART
Peripherals	POR, PWM, Voltage Detect, WDT
Number of I/O	71
Program Memory Size	48KB (48K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	2.5K x 8
Voltage - Supply (Vcc/Vdd)	2.2V ~ 5.5V
Data Converters	A/D 20x10b; D/A 2x8b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	80-LQFP
Supplier Device Package	80-LQFP (12x12)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f212d7sdfp-v2

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1.1.2 Specifications

Tables 1.1 and 1.2 outlines the Specifications for R8C/2C Group and Tables 1.3 and 1.4 outlines the Specifications for R8C/2D Group.

Table 1.1 Specifications for R8C/2C Group (1)

Item	Function	Specification
CPU	Central processing unit	R8C/Tiny series core • Number of fundamental instructions: 89 • Minimum instruction execution time: 50 ns (f(XIN) = 20 MHz, VCC = 3.0 to 5.5 V) 100 ns (f(XIN) = 10 MHz, VCC = 2.7 to 5.5 V) 200 ns (f(XIN) = 5 MHz, VCC = 2.2 to 5.5 V) • Multiplier: 16 bits × 16 bits → 32 bits • Multiply-accumulate instruction: 16 bits × 16 bits + 32 bits → 32 bits • Operation mode: Single-chip mode (address space: 1 Mbyte)
Memory	ROM, RAM	Refer to **Table 1.5 Product List for R8C/2C Group**.
Power Supply Voltage Detection	Voltage detection circuit	• Power-on reset • Voltage detection 3
I/O Ports	Programmable I/O ports	• Input-only: 2 pins • CMOS I/O ports: 71, selectable pull-up resistor • High current drive ports: 8
Clock	Clock generation circuits	3 circuits: XIN clock oscillation circuit (with on-chip feedback resistor), On-chip oscillator (high-speed, low-speed) (high-speed on-chip oscillator has a frequency adjustment function), XCIN clock oscillation circuit (32 kHz) • Oscillation stop detection: XIN clock oscillation stop detection function • Frequency divider circuit: Dividing selectable 1, 2, 4, 8, and 16 • Low power consumption modes: Standard operating mode (high-speed clock, low-speed clock, high-speed on-chip oscillator, low-speed on-chip oscillator), wait mode, stop mode
		Real-time clock (timer RE)
Interrupts		• External: 5 sources, Internal: 23 sources, Software: 4 sources • Priority levels: 7 levels
Watchdog Timer		15 bits × 1 (with prescaler), reset start selectable
Timer	Timer RA	8 bits × 1 (with 8-bit prescaler) Timer mode (period timer), pulse output mode (output level inverted every period), event counter mode, pulse width measurement mode, pulse period measurement mode
	Timer RB	8 bits × 1 (with 8-bit prescaler) Timer mode (period timer), programmable waveform generation mode (PWM output), programmable one-shot generation mode, programmable wait one-shot generation mode
	Timer RC	16 bits × 1 (with 4 capture/compare registers) Timer mode (input capture function, output compare function), PWM mode (output 3 pins), PWM2 mode (PWM output pin)
	Timer RD	16 bits × 2 (with 4 capture/compare registers) Timer mode (input capture function, output compare function), PWM mode (output 6 pins), reset synchronous PWM mode (output three-phase waveforms (6 pins), sawtooth wave modulation), complementary PWM mode (output three-phase waveforms (6 pins), triangular wave modulation), PWM3 mode (PWM output 2 pins with fixed period)
	Timer RE	8 bits × 1 Real-time clock mode (count seconds, minutes, hours, days of week), output compare mode
	Timer RF	16 bits × 1 (with capture/compare register pin and compare register pin) Input capture mode, output compare mode

1.2 Product List

Table 1.5 lists Product List for R8C/2C Group, Figure 1.1 shows a Part Number, Memory Size, and Package of R8C/2C Group, Table 1.6 lists Product List for R8C/2D Group, and Figure 1.2 shows a Part Number, Memory Size, and Package of R8C/2D Group.

Table 1.5 Product List for R8C/2C Group **Current of Dec. 2007**

Part No.	ROM Capacity	RAM Capacity	Package Type	Remarks	
R5F212C7SNFP	48 Kbytes	2.5 Kbytes	PLQP0080KB-A	N version	
R5F212C8SNFP	64 Kbytes	3 Kbytes	PLQP0080KB-A		
R5F212CASNFP	96 Kbytes	7 Kbytes	PLQP0080KB-A		
R5F212CCSNFP	128 Kbytes	7.5 Kbytes	PLQP0080KB-A		
R5F212C7SDFP	48 Kbytes	2.5 Kbytes	PLQP0080KB-A	D version	
R5F212C8SDFP	64 Kbytes	3 Kbytes	PLQP0080KB-A		
R5F212CASDFP	96 Kbytes	7 Kbytes	PLQP0080KB-A		
R5F212CCSDFP	128 Kbytes	7.5 Kbytes	PLQP0080KB-A		
R5F212C7SNXXXFP	48 Kbytes	2.5 Kbytes	PLQP0080KB-A	N version	Factory programming product(1)
R5F212C8SNXXXFP	64 Kbytes	3 Kbytes	PLQP0080KB-A		
R5F212CASNXXXFP	96 Kbytes	7 Kbytes	PLQP0080KB-A		
R5F212CCSNXXXFP	128 Kbytes	7.5 Kbytes	PLQP0080KB-A		
R5F212C7SDXXXFP	48 Kbytes	2.5 Kbytes	PLQP0080KB-A	D version	
R5F212C8SDXXXFP	64 Kbytes	3 Kbytes	PLQP0080KB-A		
R5F212CASDXXXFP	96 Kbytes	7 Kbytes	PLQP0080KB-A		
R5F212CCSDXXXFP	128 Kbytes	7.5 Kbytes	PLQP0080KB-A		

NOTE:
1. The user ROM is programmed before shipment.

Table 1.6 Product List for R8C/2D Group **Current of Dec. 2007**

Part No.	ROM Capacity		RAM Capacity	Package Type	Remarks	
	Program ROM	Data flash				
R5F212D7SNFP	48 Kbytes	1 Kbyte × 2	2.5 Kbytes	PLQP0080KB-A	N version	
R5F212D8SNFP	64 Kbytes	1 Kbyte × 2	3 Kbytes	PLQP0080KB-A		
R5F212DASNFP	96 Kbytes	1 Kbyte × 2	7 Kbytes	PLQP0080KB-A		
R5F212DCSNFP	128 Kbytes	1 Kbyte × 2	7.5 Kbytes	PLQP0080KB-A		
R5F212D7SDFP	48 Kbytes	1 Kbyte × 2	2.5 Kbytes	PLQP0080KB-A	D version	
R5F212D8SDFP	64 Kbytes	1 Kbyte × 2	3 Kbytes	PLQP0080KB-A		
R5F212DASDFP	96 Kbytes	1 Kbyte × 2	7 Kbytes	PLQP0080KB-A		
R5F212DCSDFP	128 Kbytes	1 Kbyte × 2	7.5 Kbytes	PLQP0080KB-A		
R5F212D7SNXXXFP	48 Kbytes	1 Kbyte × 2	2.5 Kbytes	PLQP0080KB-A	N version	Factory programming product(1)
R5F212D8SNXXXFP	64 Kbytes	1 Kbyte × 2	3 Kbytes	PLQP0080KB-A		
R5F212DASNXXXFP	96 Kbytes	1 Kbyte × 2	7 Kbytes	PLQP0080KB-A		
R5F212DCSNXXXFP	128 Kbytes	1 Kbyte × 2	7.5 Kbytes	PLQP0080KB-A		
R5F212D7SDXXXFP	48 Kbytes	1 Kbyte × 2	2.5 Kbytes	PLQP0080KB-A	D version	
R5F212D8SDXXXFP	64 Kbytes	1 Kbyte × 2	3 Kbytes	PLQP0080KB-A		
R5F212DASDXXXFP	96 Kbytes	1 Kbyte × 2	7 Kbytes	PLQP0080KB-A		
R5F212DCSDXXXFP	128 Kbytes	1 Kbyte × 2	7.5 Kbytes	PLQP0080KB-A		

NOTE:
1. The user ROM is programmed before shipment.

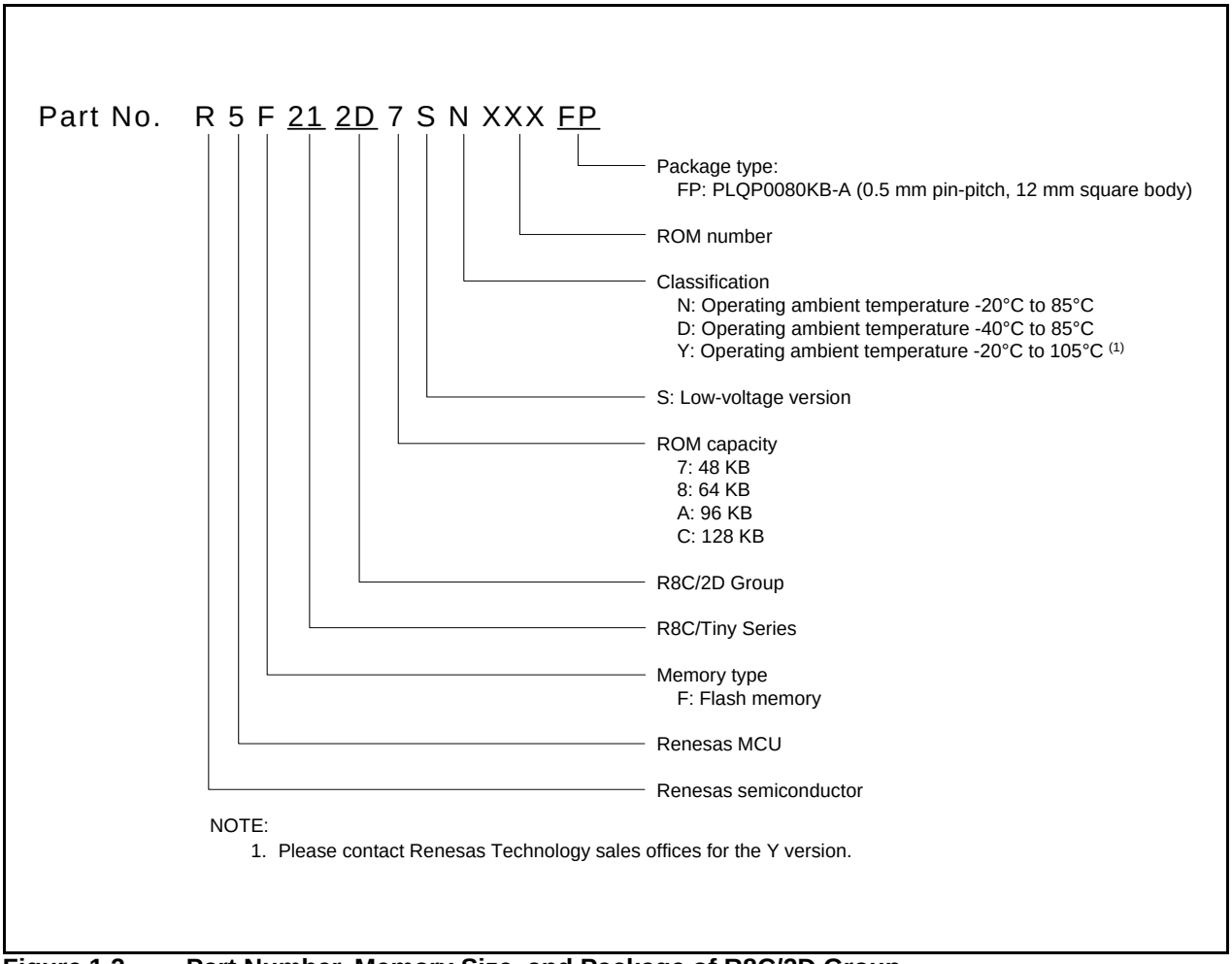
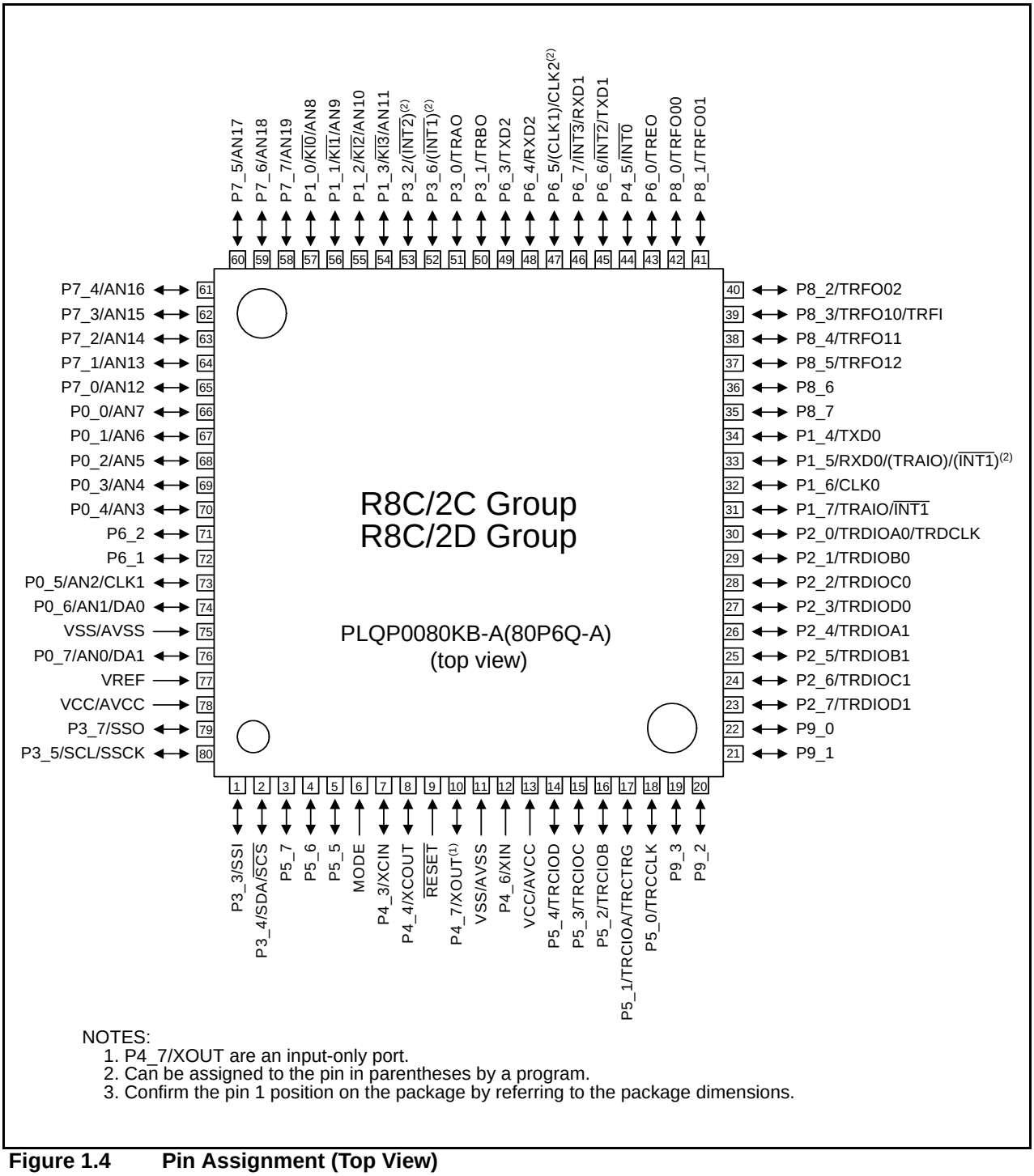


Figure 1.2 Part Number, Memory Size, and Package of R8C/2D Group

1.4 Pin Assignment

Figure 1.4 shows Pin Assignment (Top View). Tables 1.7 and 1.8 outlines the Pin Name Information by Pin Number.



NOTES:
1. P4_7/XOUT are an input-only port.
2. Can be assigned to the pin in parentheses by a program.
3. Confirm the pin 1 position on the package by referring to the package dimensions.

Figure 1.4 Pin Assignment (Top View)

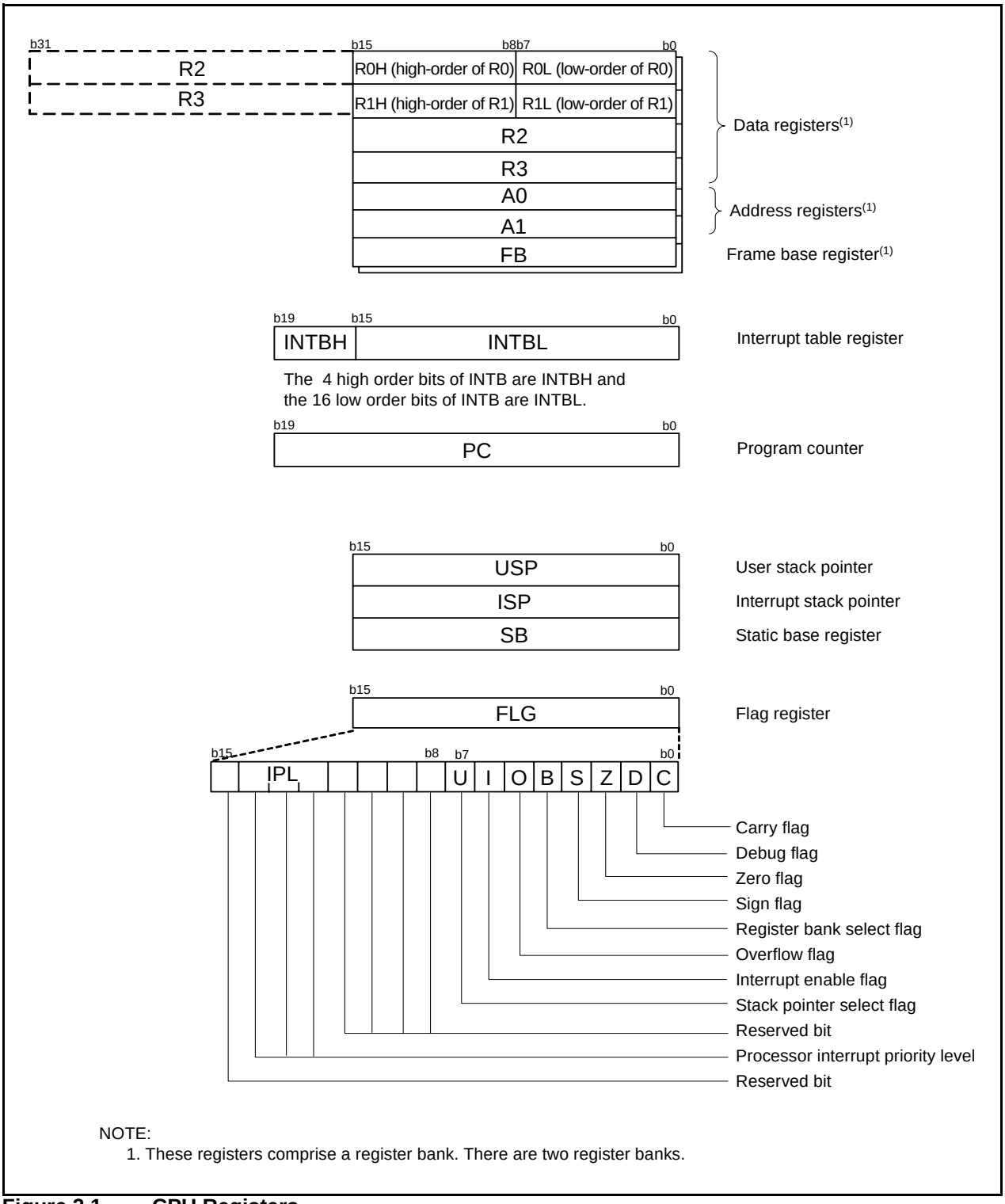
Table 1.8 Pin Name Information by Pin Number (2)

Pin Number	Control Pin	Port	I/O Pin Functions for of Peripheral Modules					
			Interrupt	Timer	Serial Interface	SSU	I^2C bus	A/D Converter, D/A Converter
46		P6_7	$\overline{INT3}$		RXD1			
47		P6_5			(CLK1)(1) /CLK2			
48		P6_4			RXD2			
49		P6_3			TXD2			
50		P3_1		TRBO				
51		P3_0		TRAO				
52		P3_6	($\overline{INT1}$)(1)					
53		P3_2	($\overline{INT2}$)(1)					
54		P1_3	$\overline{KI3}$					AN11
55		P1_2	$\overline{KI2}$					AN10
56		P1_1	$\overline{KI1}$					AN9
57		P1_0	$\overline{KI0}$					AN8
58		P7_7						AN19
59		P7_6						AN18
60		P7_5						AN17
61		P7_4						AN16
62		P7_3						AN15
63		P7_2						AN14
64		P7_1						AN13
65		P7_0						AN12
66		P0_0						AN7
67		P0_1						AN6
68		P0_2						AN5
69		P0_3						AN4
70		P0_4						AN3
71		P6_2						
72		P6_1						
73		P0_5			CLK1			AN2
74		P0_6						AN1/DA0
75	VSS/AVSS							
76		P0_7						AN0/DA1
77	VREF							
78	VCC/AVCC							
79		P3_7				SSO		
80		P3_5				SSCK	SCL	

NOTE:
1. Can be assigned to the pin in parentheses by a program.

2. Central Processing Unit (CPU)

Figure 2.1 shows the CPU Registers. The CPU contains 13 registers. R0, R1, R2, R3, A0, A1, and FB configure a register bank. There are two sets of register bank.



NOTE:
1. These registers comprise a register bank. There are two register banks.

Figure 2.1 CPU Registers

Table 4.2 SFR Information (2)[1]

Address	Register	Symbol	After reset
0040h			
0041h			
0042h			
0043h			
0044h			
0045h			
0046h			
0047h	Timer RC Interrupt Control Register	TRCIC	XXXXX000b
0048h	Timer RD0 Interrupt Control Register	TRD0IC	XXXXX000b
0049h	Timer RD1 Interrupt Control Register	TRD1IC	XXXXX000b
004Ah	Timer RE Interrupt Control Register	TREIC	XXXXX000b
004Bh	UART2 Transmit Interrupt Control Register	S2TIC	XXXXX000b
004Ch	UART2 Receive Interrupt Control Register	S2RIC	XXXXX000b
004Dh	Key Input Interrupt Control Register	KUPIC	XXXXX000b
004Eh			
004Fh	SSU/IIC Interrupt Control Register[2]	SSUIC / IICIC	XXXXX000b
0050h	Compare 1 Interrupt Control Register	CMP1IC	XXXXX000b
0051h	UART0 Transmit Interrupt Control Register	S0TIC	XXXXX000b
0052h	UART0 Receive Interrupt Control Register	S0RIC	XXXXX000b
0053h	UART1 Transmit Interrupt Control Register	S1TIC	XXXXX000b
0054h	UART1 Receive Interrupt Control Register	S1RIC	XXXXX000b
0055h	INT2 Interrupt Control Register	INT2IC	XX00X000b
0056h	Timer RA Interrupt Control Register	TRAIC	XXXXX000b
0057h			
0058h	Timer RB Interrupt Control Register	TRBIC	XXXXX000b
0059h	INT1 Interrupt Control Register	INT1IC	XX00X000b
005Ah	INT3 Interrupt Control Register	INT3IC	XX00X000b
005Bh	Timer RF Interrupt Control Register	TRFIC	XXXXX000b
005Ch	Compare 0 Interrupt Control Register	CMP0IC	XXXXX000b
005Dh	INT0 Interrupt Control Register	INT0IC	XX00X000b
005Eh	A/D Conversion Interrupt Control Register	ADIC	XXXXX000b
005Fh	Capture Interrupt Control Register	CAPIC	XXXXX000b
0060h			
0061h			
0062h			
0063h			
0064h			
0065h			
0066h			
0067h			
0068h			
0069h			
006Ah			
006Bh			
006Ch			
006Dh			
006Eh			
006Fh			
0070h			
0071h			
0072h			
0073h			
0074h			
0075h			
0076h			
0077h			
0078h			
0079h			
007Ah			
007Bh			
007Ch			
007Dh			
007Eh			
007Fh			

X: Undefined

NOTES:
1. The blank regions are reserved. Do not access locations in these regions.
2. Selected by the IICSEL bit in the PMR register.

Table 4.4 SFR Information (4)(1)

Address	Register	Symbol	After reset
00C0h			
00C1h			
00C2h			
00C3h			
00C4h			
00C5h			
00C6h			
00C7h			
00C8h			
00C9h			
00CAh			
00CBh			
00CCh			
00CDh			
00CEh			
00CFh			
00D0h			
00D1h			
00D2h			
00D3h			
00D4h			
00D5h			
00D6h			
00D7h			
00D8h	D/A Register 0	DA0	00h
00D9h			
00DAh	D/A Register 1	DA1	00h
00DBh			
00DCh	D/A Control Register	DACON	00h
00DDh			
00DEh			
00DFh			
00E0h	Port P0 Register	P0	XXh
00E1h	Port P1 Register	P1	XXh
00E2h	Port P0 Direction Register	PD0	00h
00E3h	Port P1 Direction Register	PD1	00h
00E4h	Port P2 Register	P2	XXh
00E5h	Port P3 Register	P3	XXh
00E6h	Port P2 Direction Register	PD2	00h
00E7h	Port P3 Direction Register	PD3	00h
00E8h	Port P4 Register	P4	XXh
00E9h	Port P5 Register	P5	XXh
00EAh	Port P4 Direction Register	PD4	00h
00EBh	Port P5 Direction Register	PD5	00h
00ECh	Port P6 Register	P6	XXh
00EDh			
00EEh	Port P6 Direction Register	PD6	00h
00EFh			
00F0h			
00F1h			
00F2h			
00F3h			
00F4h	Port P2 Drive Capacity Control Register	P2DRR	00h
00F5h	UART1 Function Select Register	U1SR	000000XXb
00F6h			
00F7h			
00F8h	Port Mode Register	PMR	00h
00F9h	External Input Enable Register	INTEN	00h
00FAh	INT Input Filter Select Register	INTF	00h
00FBh	Key Input Enable Register	KIEN	00h
00FCh	Pull-Up Control Register 0	PUR0	00h
00FDh	Pull-Up Control Register 1	PUR1	XX000000b
00FEh			
00FFh			

X: Undefined
NOTE:
1. The blank regions are reserved. Do not access locations in these regions.

Table 4.8 SFR Information (8)(1)

Address	Register	Symbol	After reset
01C0h			
01C1h			
01C2h			
01C3h			
01C4h			
01C5h			
01C6h			
01C7h			
01C8h			
01C9h			
01CAh			
01CBh			
01CCh			
01CDh			
01CEh			
01CFh			
01D0h			
01D1h			
01D2h			
01D3h			
01D4h			
01D5h			
01D6h			
01D7h			
01D8h			
01D9h			
01DAh			
01DBh			
01DCh			
01DDh			
01DEh			
01DFh			
01E0h			
01E1h			
01E2h			
01E3h			
01E4h			
01E5h			
01E6h			
01E7h			
01E8h			
01E9h			
01EAh			
01EBh			
01ECh			
01EDh			
01EEh			
01EFh			
01F0h			
01F1h			
01F2h			
01F3h			
01F4h			
01F5h			
01F6h			
01F7h			
01F8h			
01F9h			
01FAh			
01FBh			
01FCh			
01FDh			
01FEh			
01FFh			

NOTE:
1. The blank regions are reserved. Do not access locations in these regions.

Table 4.11 SFR Information (11)[1]

Address	Register	Symbol	After reset
0280h			
0281h			
0282h			
0283h			
0284h			
0285h			
0286h			
0287h			
0288h			
0289h			
028Ah			
028Bh			
028Ch			
028Dh			
028Eh			
028Fh			
0290h	Timer RF Register	TRF	00h
0291h			00h
0292h			
0293h			
0294h			
0295h			
0296h			
0297h			
0298h			
0299h			
029Ah	Timer RF Control Register 0	TRFCR0	00h
029Bh	Timer RF Control Register 1	TRFCR1	00h
029Ch	Capture / Compare 0 Register	TRFM0	0000h[2]
029Dh			FFFFh[3]
029Eh	Compare 1 Register	TRFM1	FFh
029Fh			FFh
02A0h			
02A1h			
02A2h			
02A3h			
02A4h			
02A5h			
02A6h			
02A7h			
02A8h			
02A9h			
02AAh			
02ABh			
02ACh			
02ADh			
02AEh			
02AFh			
02B0h			
02B1h			
02B2h			
02B3h			
02B4h			
02B5h			
02B6h			
02B7h			
02B8h			
02B9h			
02BAh			
02BBh			
02BCh			
02BDh			
02BEh			
02BFh			

NOTES:
1. The blank regions are reserved. Do not access locations in these regions.
2. After input capture mode.
3. After output compare mode.

Table 4.12 SFR Information (12)(1)

Address	Register	Symbol	After reset
02C0h	A/D Register 0	AD0	XXh
02C1h			XXh
02C2h	A/D Register 1	AD1	XXh
02C3h			XXh
02C4h	A/D Register 2	AD2	XXh
02C5h			XXh
02C6h	A/D Register 3	AD3	XXh
02C7h			XXh
02C8h			
02C9h			
02CAh			
02CBh			
02CCh			
02CDh			
02CEh			
02CFh			
02D0h			
02D1h			
02D2h			
02D3h			
02D4h	A/D Control Register 2	ADCON2	00001000b
02D5h			
02D6h	A/D Control Register 0	ADCON0	00000011b
02D7h	A/D Control Register 1	ADCON1	00h
02D8h			
02D9h			
02DAh			
02DBh			
02DCh			
02DDh			
02DEh			
02DFh			
02E0h	Port P7 Direction Register	PD7	00h
02E1h			
02E2h	Port P7 Register	P7	XXh
02E3h			
02E4h	Port P8 Direction Register	PD8	00h
02E5h	Port P9 Direction Register	PD9	X0h
02E6h	Port P8 Register	P8	XXh
02E7h	Port P9 Register	P9	XXh
02E8h			
02E9h			
02EAh			
02EBh			
02ECh			
02EDh			
02EEh			
02EFh			
02F0h			
02F1h			
02F2h			
02F3h			
02F4h			
02F5h			
02F6h			
02F7h			
02F8h			
02F9h			
02FAh			
02FBh			
02FCh	Pull-Up Control Register 2	PUR2	XXX00000b
02FDh			
02FEh			
02FFh	Timer RF Output Control Register	TRFOUT	00h

FFFFh	Option Function Select Register	OFS	(Note 2)

X: Undefined
NOTES:
1. The blank regions are reserved. Do not access locations in these regions.
2. The OFS register cannot be changed by a program. Use a flash programmer to write to it.

5. Electrical Characteristics

The electrical characteristics of N version (Topr = –20°C to 85°C) and D version (Topr = –40°C to 85°C) are listed below.
Please contact Renesas Technology sales offices for the electrical characteristics in the Y version (Topr = –20°C to 105°C).

Table 5.1 Absolute Maximum Ratings

Symbol	Parameter	Condition	Rated Value	Unit
V_{CC}/AV_{CC}	Supply voltage		–0.3 to 6.5	V
V_I	Input voltage		–0.3 to V_{CC} + 0.3	V
V_O	Output voltage		–0.3 to V_{CC} + 0.3	V
P_d	Power dissipation	T_{opr} = 25°C	700	mW
T_{opr}	Operating ambient temperature		–20 to 85 (N version) / –40 to 85 (D version)	°C
T_{stg}	Storage temperature		–65 to 150	°C

Table 5.2 Recommended Operating Conditions

Symbol	Parameter		Conditions	Standard			Unit
				Min.	Typ.	Max.	
V_{CC}/AV_{CC}	Supply voltage			2.2	–	5.5	V
V_{SS}/AV_{SS}	Supply voltage			–	0	–	V
V_{IH}	Input “H” voltage			0.8 V_{CC}	–	V_{CC}	V
V_{IL}	Input “L” voltage			0	–	0.2 V_{CC}	V
$I_{OH(sum)}$	Peak sum output “H” current	Sum of all pins $I_{OH(peak)}$		–	–	–240	mA
$I_{OH(sum)}$	Average sum output “H” current	Sum of all pins $I_{OH(avg)}$		–	–	–120	mA
$I_{OH(peak)}$	Peak output “H” current	Except P2_0 to P2_7		–	–	–10	mA
		P2_0 to P2_7		–	–	–40	mA
$I_{OH(avg)}$	Average output “H” current	Except P2_0 to P2_7		–	–	–5	mA
		P2_0 to P2_7		–	–	–20	mA
$I_{OL(sum)}$	Peak sum output “L” current	Sum of all pins $I_{OL(peak)}$		–	–	240	mA
$I_{OL(sum)}$	Average sum output “L” current	Sum of all pins $I_{OL(avg)}$		–	–	120	mA
$I_{OL(peak)}$	Peak output “L” current	Except P2_0 to P2_7		–	–	10	mA
		P2_0 to P2_7		–	–	40	mA
$I_{OL(avg)}$	Average output “L” current	Except P2_0 to P2_7		–	–	5	mA
		P2_0 to P2_7		–	–	20	mA
$f_{(XIN)}$	XIN clock input oscillation frequency		3.0 V ≤ V_{CC} ≤ 5.5 V	0	–	20	MHz
			2.7 V ≤ V_{CC} < 3.0 V	0	–	10	MHz
			2.2 V ≤ V_{CC} < 2.7 V	0	–	5	MHz
$f_{(XCIN)}$	XCIN clock input oscillation frequency		2.2 V ≤ V_{CC} ≤ 5.5 V	0	–	70	kHz
–	System clock	OCD2 = 0 XIN clock selected	3.0 V ≤ V_{CC} ≤ 5.5 V	0	–	20	MHz
			2.7 V ≤ V_{CC} < 3.0 V	0	–	10	MHz
			2.2 V ≤ V_{CC} < 2.7 V	0	–	5	MHz
		OCD2 = 1 On-chip oscillator clock selected	FRA01 = 0 Low-speed on-chip oscillator clock selected	–	125	–	kHz
			FRA01 = 1 High-speed on-chip oscillator clock selected 3.0 V ≤ V_{CC} ≤ 5.5 V	–	–	20	MHz
			FRA01 = 1 High-speed on-chip oscillator clock selected 2.7 V ≤ V_{CC} ≤ 5.5 V	–	–	10	MHz
			FRA01 = 1 High-speed on-chip oscillator clock selected 2.2 V ≤ V_{CC} ≤ 5.5 V	–	–	5	MHz

NOTES:
1. V_{CC} = 2.2 to 5.5 V at T_{opr} = –20 to 85°C (N version) / –40 to 85°C (D version), unless otherwise specified.
2. The average output current indicates the average value of current measured during 100 ms.

Table 5.6 Flash Memory (Data flash Block A, Block B) Electrical Characteristics(4)

Symbol	Parameter	Conditions	Standard			Unit
			Min.	Typ.	Max.	
–	Program/erase endurance(2)		10,000(3)	–	–	times
–	Byte program time (program/erase endurance ≤ 1,000 times)		–	50	400	µs
–	Byte program time (program/erase endurance > 1,000 times)		–	65	–	µs
–	Block erase time (program/erase endurance ≤ 1,000 times)		–	0.2	9	s
–	Block erase time (program/erase endurance > 1,000 times)		–	0.3	–	s
$t_{d(SR-SUS)}$	Time delay from suspend request until suspend		–	–	97+CPU clock × 6 cycles	µs
–	Interval from erase start/restart until following suspend request		650	–	–	µs
–	Interval from program start/restart until following suspend request		0	–	–	ns
–	Time from suspend until program/erase restart		–	–	3+CPU clock × 4 cycles	µs
–	Program, erase voltage		2.7	–	5.5	V
–	Read voltage		2.2	–	5.5	V
–	Program, erase temperature		–20(8)	–	85	°C
–	Data hold time(9)	Ambient temperature = 55 °C	20	–	–	year

NOTES:
1. V_{CC} = 2.7 to 5.5 V at T_{opr} = –20 to 85°C (N version) / –40 to 85°C (D version), unless otherwise specified.
2. Definition of programming/erasure endurance
   The programming and erasure endurance is defined on a per-block basis.
   If the programming and erasure endurance is n (n = 100 or 10,000), each block can be erased n times. For example, if 1,024 1-byte writes are performed to block A, a 1 Kbyte block, and then the block is erased, the programming/erasure endurance still stands at one.
   However, the same address must not be programmed more than once per erase operation (overwriting prohibited).
3. Endurance to guarantee all electrical characteristics after program and erase. (1 to Min. value can be guaranteed).
4. Standard of block A and block B when program and erase endurance exceeds 1,000 times. Byte program time to 1,000 times is the same as that in program ROM.
5. In a system that executes multiple programming operations, the actual erasure count can be reduced by writing to sequential addresses in turn so that as much of the block as possible is used up before performing an erase operation. For example, when programming groups of 16 bytes, the effective number of rewrites can be minimized by programming up to 128 groups before erasing them all in one operation. It is also advisable to retain data on the erase count of each block and limit the number of erase operations to a certain number.
6. If an error occurs during block erase, attempt to execute the clear status register command, then execute the block erase command at least three times until the erase error does not occur.
7. Customers desiring program/erase failure rate information should contact their Renesas technical support representative.
8. –40°C for D version.
9. The data hold time includes time that the power supply is off or the clock is not supplied.

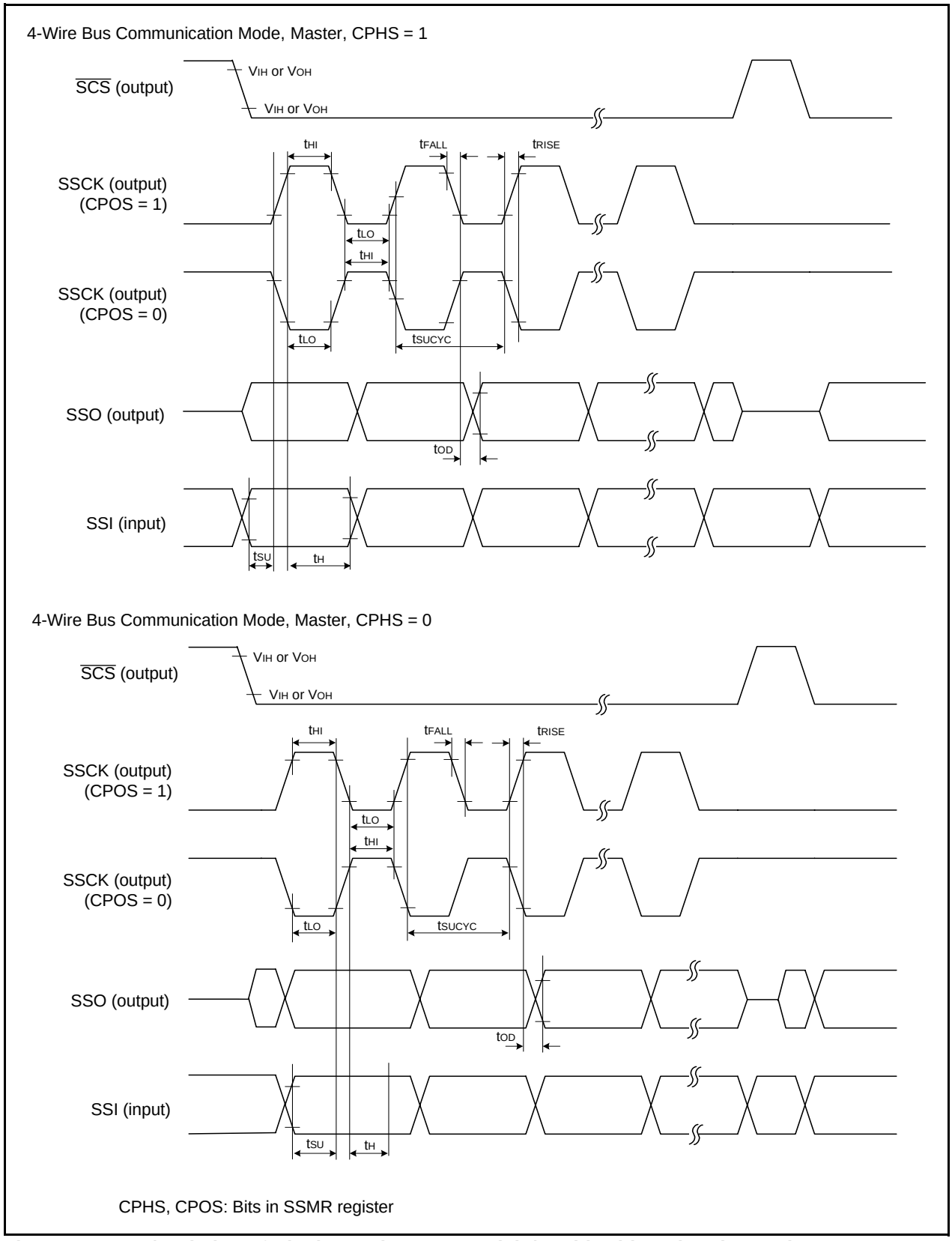


Figure 5.4 I/O Timing of Clock Synchronous Serial I/O with Chip Select (Master)

Table 5.23 Electrical Characteristics (3) [Vcc = 3 V]

Symbol	Parameter		Condition		Standard			Unit
					Min.	Typ.	Max.	
V_{OH}	Output “H” voltage	Except P2_0 to P2_7, XOUT	I_{OH} = –1 mA		Vcc – 0.5	–	Vcc	V
		P2_0 to P2_7	Drive capacity HIGH	I_{OH} = –5 mA	Vcc – 0.5	–	Vcc	V
			Drive capacity LOW	I_{OH} = –1 mA	Vcc – 0.5	–	Vcc	V
		XOUT	Drive capacity HIGH	I_{OH} = –0.1 mA	Vcc – 0.5	–	Vcc	V
			Drive capacity LOW	I_{OH} = –50 µA	Vcc – 0.5	–	Vcc	V
V_{OL}	Output “L” voltage	Except P2_0 to P2_7, XOUT	I_{OL} = 1 mA		–	–	0.5	V
		P2_0 to P2_7	Drive capacity HIGH	I_{OL} = 5 mA	–	–	0.5	V
			Drive capacity LOW	I_{OL} = 1 mA	–	–	0.5	V
		XOUT	Drive capacity HIGH	I_{OL} = 0.1 mA	–	–	0.5	V
			Drive capacity LOW	I_{OL} = 50 µA	–	–	0.5	V
V_{T+}-V_{T-}	Hysteresis	$\overline{INT0}$, $\overline{INT1}$, $\overline{INT2}$, $\overline{INT3}$, $\overline{KI0}$, $\overline{KI1}$, $\overline{KI2}$, $\overline{KI3}$, TRAIO, TRFI, RXD0, RXD1, CLK0, CLK1, CLK2, SSI, SCL, SDA, SSO			0.1	0.3	–	V
		$\overline{RESET}$			0.1	0.4	–	V
I_{IH}	Input “H” current		VI = 3 V		–	–	4.0	µA
I_{IL}	Input “L” current		VI = 0 V		–	–	–4.0	µA
R_{PULLUP}	Pull-up resistance		VI = 0 V		66	160	500	kΩ
R_{fXIN}	Feedback resistance	XIN			–	3.0	–	MΩ
R_{fXCIN}	Feedback resistance	XCIN			–	18	–	MΩ
V_{RAM}	RAM hold voltage		During stop mode		1.8	–	–	V

NOTE:
1. Vcc =2.7 to 3.3 V at T_{opr} = –20 to 85°C (N version) / –40 to 85°C (D version), f(XIN) = 10 MHz, unless otherwise specified.

Table 5.24 Electrical Characteristics (4) [Vcc = 3 V]
(Topr = –20 to 85°C (N version) / –40 to 85°C (D version), unless otherwise specified.)

Symbol	Parameter	Condition		Standard			Unit
				Min.	Typ.	Max.	
ICC	Power supply current (VCC = 2.7 to 3.3 V) Single-chip mode, output pins are open, other pins are VSS	High-speed clock mode	XIN = 10 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz No division	–	5.5	–	mA
			XIN = 10 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8	–	2	–	mA
		High-speed on-chip oscillator mode	XIN clock off High-speed on-chip oscillator on fOCO = 10 MHz Low-speed on-chip oscillator on = 125 kHz No division	–	5.5	11	mA
			XIN clock off High-speed on-chip oscillator on fOCO = 10 MHz Low-speed on-chip oscillator on = 125 kHz Divide-by-8	–	2.2	–	mA
		Low-speed on-chip oscillator mode	XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8, FMR47 = 1	–	145	400	µA
		Low-speed clock mode	XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator off XCIN clock oscillator on = 32 kHz FMR47 = 1	–	145	400	µA
			XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator off XCIN clock oscillator on = 32 kHz Program operation on RAM Flash memory off, FMSTP = 1	–	30	–	µA
		Wait mode	XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz While a WAIT instruction is executed Peripheral clock operation VCA27 = VCA26 = VCA25 = 0 VCA20 = 1	–	28	85	µA
			XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz While a WAIT instruction is executed Peripheral clock off VCA27 = VCA26 = VCA25 = 0 VCA20 = 1	–	17	50	µA
			XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator off XCIN clock oscillator on = 32 kHz (high drive) While a WAIT instruction is executed VCA27 = VCA26 = VCA25 = 0 VCA20 = 1	–	3.3	–	µA
			XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator off XCIN clock oscillator on = 32 kHz (low drive) While a WAIT instruction is executed VCA27 = VCA26 = VCA25 = 0 VCA20 = 1	–	2.1	–	µA
		Stop mode	XIN clock off, Topr = 25°C High-speed on-chip oscillator off Low-speed on-chip oscillator off CM10 = 1 Peripheral clock off VCA27 = VCA26 = VCA25 = 0	–	0.65	3.0	µA
			XIN clock off, Topr = 85°C High-speed on-chip oscillator off Low-speed on-chip oscillator off CM10 = 1 Peripheral clock off VCA27 = VCA26 = VCA25 = 0	–	1.65	–	µA

Table 5.31 Electrical Characteristics (6) [Vcc = 2.2 V]
(Topr = –20 to 85°C (N version) / –40 to 85°C (D version), unless otherwise specified.)

Symbol	Parameter	Condition		Standard			Unit
				Min.	Typ.	Max.	
ICC	Power supply current (VCC = 2.2 to 2.7 V) Single-chip mode, output pins are open, other pins are VSS	High-speed clock mode	XIN = 5 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz No division	–	2.5	–	mA
			XIN = 5 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8	–	1	–	mA
		High-speed on-chip oscillator mode	XIN clock off High-speed on-chip oscillator on fOCO = 5 MHz Low-speed on-chip oscillator on = 125 kHz No division	–	4	–	mA
			XIN clock off High-speed on-chip oscillator on fOCO = 5 MHz Low-speed on-chip oscillator on = 125 kHz Divide-by-8	–	1.7	–	mA
		Low-speed on-chip oscillator mode	XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8, FMR47 = 1	–	110	300	µA
		Low-speed clock mode	XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator off XCIN clock oscillator on = 32 kHz FMR47 = 1	–	125	350	µA
			XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator off XCIN clock oscillator on = 32 kHz Program operation on RAM Flash memory off, FMSTP = 1	–	27	–	µA
		Wait mode	XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz While a WAIT instruction is executed Peripheral clock operation VCA27 = VCA26 = VCA25 = 0 VCA20 = 1	–	20	60	µA
			XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz While a WAIT instruction is executed Peripheral clock off VCA27 = VCA26 = VCA25 = 0 VCA20 = 1	–	12	40	µA
			XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator off XCIN clock oscillator on = 32 kHz (high drive) While a WAIT instruction is executed VCA27 = VCA26 = VCA25 = 0 VCA20 = 1	–	2.8	–	µA
			XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator off XCIN clock oscillator on = 32 kHz (low drive) While a WAIT instruction is executed VCA27 = VCA26 = VCA25 = 0 VCA20 = 1	–	1.9	–	µA
		Stop mode	XIN clock off, Topr = 25°C High-speed on-chip oscillator off Low-speed on-chip oscillator off CM10 = 1 Peripheral clock off VCA27 = VCA26 = VCA25 = 0	–	0.6	3.0	µA
			XIN clock off, Topr = 85°C High-speed on-chip oscillator off Low-speed on-chip oscillator off CM10 = 1 Peripheral clock off VCA27 = VCA26 = VCA25 = 0	–	1.60	–	µA

Timing requirements
(Unless Otherwise Specified: Vcc = 2.2 V, Vss = 0 V at Topr = 25°C) [Vcc = 2.2 V]

Table 5.32 XIN Input, XCIN Input

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(XIN)}$	XIN input cycle time	200	–	ns
$t_{WH(XIN)}$	XIN input “H” width	90	–	ns
$t_{WL(XIN)}$	XIN input “L” width	90	–	ns
$t_{c(XCIN)}$	XCIN input cycle time	14	–	µs
$t_{WH(XCIN)}$	XCIN input “H” width	7	–	µs
$t_{WL(XCIN)}$	XCIN input “L” width	7	–	µs

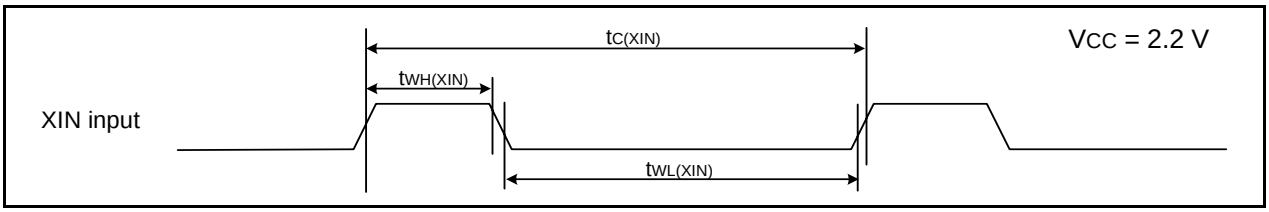


Figure 5.18 XIN Input and XCIN Input Timing Diagram when Vcc = 2.2 V

Table 5.33 TRAIO Input, $\overline{\text{INT1}}$ Input

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(TRAIO)}$	TRAIO input cycle time	500	–	ns
$t_{WH(TRAIO)}$	TRAIO input “H” width	200	–	ns
$t_{WL(TRAIO)}$	TRAIO input “L” width	200	–	ns

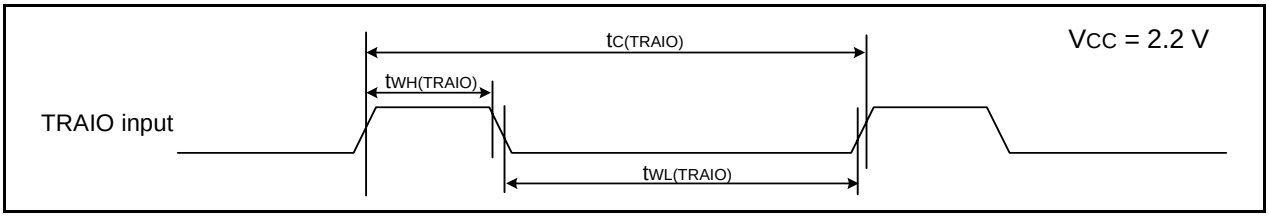


Figure 5.19 TRAIO Input and $\overline{\text{INT1}}$ Input Timing Diagram when Vcc = 2.2 V

Table 5.34 TRFI Input

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(TRFI)}$	TRFI input cycle time	2000(1)	–	ns
$t_{WH(TRFI)}$	TRFI input “H” width	1000(2)	–	ns
$t_{WL(TRFI)}$	TRFI input “L” width	1000(2)	–	ns

NOTES:
1. When using timer RF input capture mode, adjust the cycle time to (1/timer RF count source frequency × 3) or above.
2. When using timer RF input capture mode, adjust the pulse width to (1/timer RF count source frequency × 1.5) or above.

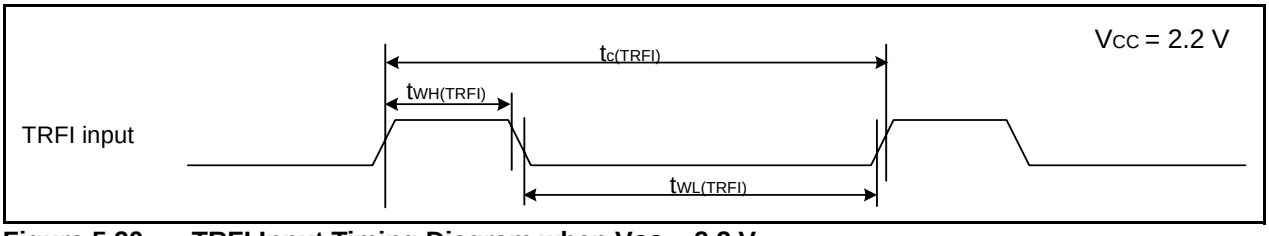


Figure 5.20 TRFI Input Timing Diagram when Vcc = 2.2 V